Contents

Editors' preface ix

SECTION I. EPITAXIAL GROWTH AND CHARACTERIZATION

I.1. Materials for lasers

Growth issues for blue–green laser diodes *
R.L. Gunshor, J. Han, G.C. Hua, A.V. Nurmikko and H. Jeon 1

Novel ZnCdSe/MgZnCdSe compound system grown on InP substrates by MBE and theoretical investigation of 550–640 nm range ZnCdSe/MgZnCdSe lasers
I. Nomura, T. Morita, A. Kikuchi and K. Kishino 11

Composition, stoichiometry and growth rate control in molecular beam epitaxy of ZnSe based ternary and quaternary alloys
S.V. Ivanov, S.V. Sorokin, P.S. Kop'ev, J.R. Kim, H.D. Jung and H.S. Park 16

Optical, structural and lattice dynamical properties of epitaxial $Zn_{1-y}Mg_yS_xSe_{1-x}$ layers grown by metalorganic vapour phase epitaxy
H. Hamadeh, J. Söllner, J. Hermans, U. Küster, J. Woitok, J. Geurts, B. Bollig and M. Heuken 21

(Cd,Zn)Se multi-quantum-well LEDs: homoepitaxy on ZnSe substrates and heteroepitaxy on (In,Ga)As/GaAs buffer layers
H. Wenisch, K. Schüll, T. Behr, D. Hommel, G. Landwehr, D. Siche, P. Rudolph and H. Hartmann 26

A comparison of Mg and Ca for quaternary cladding layers in ZnSe based laser diodes
B. Jobst, U. Lunz, D. Hommel and G. Landwehr 32

MBE growth of ZnCdSe and MgZnCdSe alloys on InP substrates with a GaInAs buffer-layer
K. Naniwae, H. Iwata, N. Kuroda, K. Yashiki, M. Kuramoto and T. Suzuki 36

Distribution of chalcogen atoms in ZnSSe and ZnMgSSe: an EXAFS study
T. Maruyama, T. Ogawa, K. Akimoto, Y. Kitajima, S. Itoh and A. Ishibashi 41

Optical properties of wide bandgap ZnHgSSe layers grown by molecular beam epitaxy
K. Hara, K. Yamamoto, Y. Eguchi, M. Usui, H. Munekata and H. Kukimoto 45

Optical characterization of ZnMnSSe quaternary alloys for visible light emitting devices
J.W. Hutchins, B. Parameshwaran, B.J. Skromme, D.J. Smith and S. Sivananthan 50

Epitaxy of $Zn_{1-x}Mg_xSe_yTe_{1-y}$ on (100)InAs
M.Th. Litz, K. Watanabe, M. Korn, H. Ress, U. Lunz, W. Ossau, A. Waag, G. Landwehr, Th. Walter, B. Neubauer, D. Gerthsen and U. Schüssler 54

I.2. Characterization

Heteroepitaxial CdTe(111) grown by MBE on nominally flat and misoriented Si(001) substrates: characterization by electron microscopy and optical methods
S.-C.Y. Tsen, D.J. Smith, J.W. Hutchins, B.J. Skromme, Y.P. Chen and S. Sivananthan 58

Photoluminescence properties of ZnS epilayers grown by metalorganic molecular beam epitaxy
C.J. Summers, W. Tong, T.K. Tran, W. Ogle, W. Park and B.K. Wagner 64

MOCVD grown CdTe investigated by photoluminescence and PAC
T. Filz, J. Hamann, R. Müller, V. Ostheimer, H. Wolf and Th. Wichert 68

Hydrogen–arsenic interactions in MOVPE-grown CdTe: effects of rapid thermal annealing
L. Svob, Y. Marfaing, B. Clerjaud, D. Côte, A. Lebkiri and R. Druilhe 72

Heteroepitaxy of CdTe on {211}Si substrates by molecular beam epitaxy
A. Million, N.K. Dhar and J.H. Dinan 76

* Invited paper.

Wurtzite $Zn_xCd_{1-x}S$ layers grown by combining MBE and hot-wall beam epitaxy
M. Hetterich, S. Petillon, W. Petri, A. Dinger, M. Grün and C. Klingshirn 81
Molecular beam epitaxial growth of ZnSe(111) films on misoriented GaAs(111)A substrates
N. Matsumura, K. Maemura, T. Mori and J. Saraie 85
Near band-edge emission in strained MBE-grown ZnS
K.B. Ozanyan, L. May, J.E. Nicholls, J.H.C. Hogg, W.E. Hagston, B. Lunn and D.E. Ashenford 89
MnS/ZnSe on GaAs grown by molecular beam epitaxy
S. Sivananthan, L. Wang, R. Sporken, J. Chen, B.J. Skromme and D.J. Smith 94
Strain relaxation in selectively grown ZnSe-epilayers on patterned GaAs-substrates
L. Parthier, H. Wissmann and M. von Ortenberg 99
Microprobe Raman study of the variation of LO phonon frequency with the Cd concentration in the ternary compound $Zn_{1-x}Cd_xSe$
W. Meredith, G. Horsburgh, G.D. Brownlie, K.A. Prior, B.C. Cavenett, W. Rothwell and A.J. Dann 103
High purity ZnSe epilayers grown by atmospheric double zone metalorganic atomic layer epitaxy
C.D. Lee, S.I. Min and S.K. Chang 108
Influence of lattice relaxation on the properties of ZnSe/ZnS single quantum wells by MOVPE
S.K. Chang, C.D. Lee, S.I. Min, E.D. Sim and Y.S. Joh 112
MOVPE growth of zincblende magnesium sulphide
L. Konczewicz, P. Bigenwald, T. Cloitre, M. Chibane, R. Ricou, P. Testud, O. Briot and R.L. Aulombard 117
MOVPE growth of (100) CdZnTe layers using DiPZn
K. Yasuda, M. Minamide, K. Kawamoto and T. Maejima 121
X-ray measurements of strains in MOCVD grown thin cap layers of CdTe
A. Raizman, A. Sher and G. Cinader 126
Growth of p-type ZnSe by metalorganic vapor phase epitaxy using ethylazide as a new nitrogen source
K. Inoue, K. Yanashima, T. Takahashi, J.S. Hwang, K. Hara, H. Munekata and H. Kukimoto 130
Structural characterization and MOVPE growth of ZnCdSe and ZnSSe layers, quantum wells and superlattices
M.J. Kastner, B. Hahn, C. Auchter, M. Deufel, A. Rosenauer and W. Gebhardt 134
Methylallyltelluride in the MOVPE of ZnTe: dissociation mechanisms and layer growth
B. Qu'Hen, W.S. Kuhn, A. Lusson and O. Gorochov 138
Optimization of the structural and optical properties of ZnS epilayers grown on (100)GaAs by MOVPE
G. Leo, N. Lovergine, P. Prete, M. Longo, R. Cingolani, A.M. Mancini, F. Romanato and A.V. Drigo 144
Photoactive defect-related I_v luminescence line observed in ZnSe/GaAs layers grown by molecular beam epitaxy
M. Yoneta, M. Ohishi, H. Kobashi and H. Saito 148
Raman monitoring of ternary compound formation: ZnS_xSe_{1-x} on GaAs(100)
D. Drews, A. Schneider, K. Horn and D.R.T. Zahn 152

SECTION II. GROWTH AND CHARACTERIZATION

II.1. Bulk crystals

Growth by solid phase recrystallization and assessment of large ZnSe crystals of high purity and structural perfection
R. Triboulet, J.O. Ndap, A. Tromson-Carli, P. Lemasson, C. Morhain and G. Neu 156
Influence of convection on zinc selenide single crystal growth by chemical vapour transport
K. Böttcher, H. Hartmann and R. Röstel 161
Luminescence of $Zn_{1-x}Mg_xSe$, $Zn_{1-x}Mg_xSe$:Al and $Zn_{1-x}Mg_xSe$:I mixed crystals grown by Bridgman method
F. Firszt, S. Łęgowski, H. Męczyńska, H.L. Oczkowski, W. Osińska, J. Szatkowski, W. Paszkowicz and Z.M. Spolnik 167
Preparation and photoluminescence study of high purity CdTe single crystals
B. Yang, Y. Ishikawa, T. Miki, Y. Doumae, T. Tomizono and M. Isshiki 171
Investigation of the transition range in seeded vapour grown ZnSe crystals
U. Geissler, H. Hartmann, E. Krause and D. Siche 175
Vapour growth of II–VI solid solution single crystals
Yu.V. Korostelin, V.I. Kozlovsky, A.S. Nasibov and P.V. Shapkin 181
Atomic configuration and far-infrared optical spectra of lattice vibrations of Zn–Te and Cd–Te modes in$Cd_{1-x}Zn_x$ Te($x = 0$–0.2)
A.I. Belogorokhov, L.I. Belogorokhova, A.G. Belov, V.M. Lakeenkov, L.M. Liberant and N.A. Smirnova 186
Growth and characterization of the ternary ZnSe-based compounds obtained by low temperature vapour transport
A. Mycielski, L. Kowalczyk and B. Witkowska 191

II.2. Thin films

Properties of ZnO layers deposited by "photo-assisted" spray pyrolysis
S. Oktik, G.J. Russell and A.W. Brinkman 195
Layer-by-layer electrodeposition of cadmium telluride onto silicon
F. Jackson, L.E.A. Berlouis and P. Rocabois 200
Miscibility gap in $Zn_xSr_{1-x}S$, $Zn_xCa_{1-x}S$ and $Zn_xSr_{1-x}Se$ thin films
M. Kitagawa, S.T. Lee, K. Ichino and H. Kobayashi 205
Preparation of ZnO films by spray pyrolysis
A.J.C. Fiddes, K. Durose, A.W. Brinkman, J. Woods, P.D. Coates and A.J. Banister 210

SECTION III. DOPING

III.1. Nitrogen doping

Nitrogen doping and carrier compensation in p-ZnSe *
T. Yao, Z. Zhu, Y.H. Wu, C.D. Song, F. Nishiyama, K. Kimura, H. Kajiyama, S. Miwa and T. Yasuda 214
Fundamental doping limits in wide gap II–VI compounds *
W. Faschinger 221
Spin-flip Raman scattering studies of doped epitaxial zinc selenide *
D. Wolverson, P.J. Boyce, C.M. Townsley, B. Schlichtherle and J.J. Davies 229
Light emitting diodes from MOVPE-grown p- and n-doped II–VI compounds *
W. Gebhardt, B. Hahn, H. Stanzl and M. Deufel 238
Activation of shallow dopants in II–VI compounds
W. Walukiewicz 244
Compensating processes in nitrogen δ-doped ZnSe layers studied by photoluminescence and photoluminescence excitation spectroscopy
Z. Zhu, G.D. Brownlie, G. Horsburgh, P.J. Thompson, S.Y. Wang, K.A. Prior and B.C. Cavenett 248
Intensity-dependent energy and lineshape variation of donor–acceptor-pair bands in highly compensated ZnSe:N
P. Bäume, J. Gutowski, E. Kurtz, D. Hommel and G. Landwehr 252
Low-resistivity p-type ZnSe, ZnSSe and MgZnSSe grown by gas-source molecular beam epitaxy
M. Imaizumi, H. Kuroki, Y. Endoh, M. Suita, K. Ohtsuka, T. Isu, H. Namizaki and M. Nunoshita 257
Real time monitoring of growth and p-type doping processes in MOVPE of ZnSe
M. Miyachi, Y. Ohira, S. Komatsu, M. Kurihara, N. Shimoyama, M. Kobayashi, Y. Kato and A. Yoshikawa 261
Comparison of hydrogen passivation of ZnSe:N using gas source and conventional molecular beam epitaxy
E. Ho, G.S. Petrich and L.A. Kolodziejski 266
Plasma nitrogen doping efficiency in molecular beam epitaxy of tellurium-based II–VI compounds
T. Baron, K. Saminadayar and S. Tatarenko 271
Raman spectroscopy and selective pair luminescence on ZnSe:N
D. Albert, J. Kraus, E. Kurtz, S. Einfeldt and D. Hommel 276
Hole traps in nitrogen-doped ZnSe epitaxial layers
T. Matsumoto, K. Egashira and T. Kato 280
Doping efficiency and plasma analysis of a nitrogen electron cyclotron resonance plasma
M. Grün, N. Sadeghi, J. Cibert, Y. Genuist and A. Tserepi 284
Novel results on compensation processes in ZnSe:N
E. Kurtz, J. Nürnberger, B. Jobst, H. Baumann, M. Kuttler, S. Einfeldt, D. Hommel, G. Landwehr, K. Bethge and D. Bimberg 289
Electrical characterization of doped ZnSe-based heterostructures grown by MOVPE
S. Lampe, M. Germain, J. Söllner, W. Taudt, R. Evrard and M. Heuken 293
Compensation in heavily N-doped ZnSe: a luminescence study
C. Kothandaraman, G.F. Neumark and R.M. Park 298
Strain-dependent Zeeman effect of the nitrogen acceptor bound exciton in ZnSe-epilayers
A. Hoffmann, D. Wiesmann, I. Loa, R. Heitz, U.W. Pohl, I. Broser, L. Worschech, E. Kurtz, D. Hommel, G. Landwehr, D. Hoffmann and B.K. Meyer 302
Influence of compensation on the luminescence of nitrogen-doped ZnSe epilayers grown by MOVPE
R. Heitz, E. Moll, V. Kutzer, D. Wiesmann, B. Lummer, A. Hoffmann, I. Broser, P. Bäume, W. Taudt, J. Söllner and M. Heuken 307
Effects of annealing atmosphere and temperature on acceptor activation in ZnSe:N grown by photoassisted MOVPE
K.-i. Ogata, D. Kawaguchi, T. Kera, Sz. Fujita and Sg. Fujita 312

Nitrogen-doped ZnSe grown by low-pressure metalorganic chemical vapor deposition with alternate growth and active nitrogen doping
K. Morimoto 317
Photoluminescence excitation spectroscopic studies of nitrogen doped ZnSe
G.D. Brownlie, Z. Zhu, G. Horsburgh, T. Steele, P.J. Thompson, J.M. Wallace, K.A. Prior and B.C. Cavenett 321
Optically detected magnetic resonance of MBE-grown ZnSe:N
T.A. Kennedy, E.R. Glaser, S.W. Brown, B.C. Cavenett and K.A. Prior 325
The role of defects on radiative transitions in nitrogen doped ZnSe
I.S. Hauksson, J. Suda, M. Tsuka, Y. Kawakami, Sz. Fujita and Sg. Fujita 329
Nitrogen-doped ZnSe(100) films grown by molecular beam epitaxy using a capacitively coupled plasma cell
J. Saraie, K. Yamawaki, N. Matsumura and A. Ikehara 334

III.2. General

Intrinsic defects in II–VI semiconductors *
G.D. Watkins 338
DX centres in CdZnTe:Cl and their applications
T. Thio, J.W. Bennett, D.J. Chadi, R.A. Linke and P. Becla 345
Extended X-ray absorption fine structure study of heavily Cl doped ZnSe
K. Akimoto, T. Ogawa, T. Maruyama and Y. Kitajima 350
Electrical and structural properties of Cl-doped ZnSe MBE-grown with various doping techniques
Jin-Sang Kim, Gyeung-Ho Kim, Sang-Hee Suh and Su-Jin Chung 354
Boron implantation into CdTe
E. Oldekop, S. Hermann, G. Sulzer, F. Niedermeyer, M. Wienecke and W.-D. Zeitz 359
Optical investigation of Cl-doped ZnSe and ZnS_xSe_{1-x} layers grown by metalorganic vapour phase epitaxy
J. Hermans, J. Woitok, J. Geurts, J. Söllner, M. Heuken, H. Stanzl and W. Gebhardt 363
Strong room temperature excitonic resonance in CdTe:I
T.K. Tran, J.W. Tomm, N.C. Giles, B.K. Wagner, A. Parikh and C.J. Summers 368
Complex formation at indium donors in p-CdTe
U. Reislöhner, N. Achtziger, M. Rüb and W. Witthuhn 372
On the growth mechanism of Li- and Na-doped Zn chalcogenides on GaAs(001) by means of molecular beam epitaxy
M. Ohishi, M. Yoneta, S. Ishii, M. Ohura, Y. Hiroe and H. Saito 376
Spatial correlations of In-donor charges in CdTe layers
T. Suski, P. Wiśniewski, E. Litwin-Staszewska, D. Wasik, J. Przybytek, M. Baj, G. Karczewski, T. Wojtowicz, A. Zakrzewski and J. Kossut 380
Doping and compensation phenomena of Ag in CdTe
J. Bollmann, M. Wienecke, J. Röhrich and H. Kerkow 384
Acceptor defects and annealing behavior in indium doped $Cd_{1-x}Zn_xTe$ ($x > 0.7$)
K. Suzuki, K. Inagaki, S. Seto, I. Tsubono, N. Kimura, T. Sawada and K. Imai 388
Hydrostatic pressure study of indium DX-like centers in MBE-grown CdTe and CdMnTe layers
D. Wasik, J. Przybytek, M. Baj, G. Karczewski, T. Wojtowicz and J. Kossut 392
Characterization of self-compensating defect complexes in MBE grown CdTe by magnetoluminescence spectroscopy
L. Worschech, W. Ossau, F. Fischer, A. Waag and G. Landwehr 397
A study of the excess carrier dynamics in ZnSe based structures grown by molecular beam epitaxy
J.S. Massa, G.S. Buller, A.C. Walker, J. Simpson, G. Horsburgh, J.T. Mullins, K.A. Prior and B.C. Cavenett 402
Drift mobilities in chlorine doped $Cd_{0.8}Zn_{0.2}Te$
K. Suzuki, N. Akita, S. Dairaku, S. Seto, T. Sawada and K. Imai 406
Electron mobilities in MOVPE-grown ZnSe quantum wells
M. Drechsler, D.M. Hofmann, D. Volm, W. Stadler, G. Steude, B.K. Meyer, W. Taudt, J. Söllner and M. Heuken 410
Magneto-optical investigation of the shallow lithium acceptor in zinc selenide
U.W. Pohl, D. Wiesmann, G.H. Kudlek, B. Litzenburger and A. Hoffmann 414

SECTION IV. QUANTUM WELLS AND SUPERLATTICES

CdTe quantum wires achieved by strain-induced lateral confinement *
H. Mariette, D. Brinkmann, G. Fishman, C. Gourgon, L.S. Dang and A. Löffler 418
Electronic and optical properties of the fractional ZnTe-monolayer superlattice structures
Q.X. Zhao, N. Magnea and J.L. Pautrat 425

Time-resolved luminescence spectroscopy of recombination dynamics in a ZnSSe doping superlattice
Y. Kawakami, T. Onishi, S. Yamaguchi, H. Kurusu, Sz. Fujita and Sg. Fujita 429
Fabrication and characterisation of dry etched CdTe/CdMnTe quantum dots
A. Ribayrol, Y.S. Tang, H.P. Zhou, D. Coquillat, C.M. Sotomayor Torres, J.P. Lascaray, B. Lunn, D.E. Ashenford, G. Feuillet and J. Cibert 434
Optimization and optical studies of ZnCdSe–ZnSe heterostructures grown by MOVPE
T. Cloitre, L. Aigouy, B. Gil, O. Briot, N. Briot, J.P. Alexis and R.L. Aulombard 438
Effects of electron localisation on the magneto-optical properties of modulation doped CdTe/CdZnTe quantum wells
K. Kheng, R.T. Cox, T. Baron, K. Saminadayar and S. Tatarenko 443
Optical properties of ZnS and ZnCdS/ZnS MQW grown by molecular beam epitaxy on GaAs and CaF_2 substrates
T. Yasuda, T. Yasui and Y. Segawa 447
Photoluminescence of CdZnSe/ZnSe quantum well structures fabricated by reactive ion etching
H. Straub, G. Brunthaler, W. Faschinger, G. Bauer and C. Vieu 451
Room temperature emission in narrow (14 nm) $Cd_{0.35}Zn_{0.65}Se$/ZnSe quantum wires with strong lateral confinement effects
G. Bacher, M. Illing, R. Spiegel, T. Kümmell, K. Herz, A. Forchel, B. Jobst, D. Hommel and G. Landwehr 455
Piezoelectric effect in ZnSe/ZnCdSe quantum wells grown on (211)B GaAs
S.Y. Wang, P.J. Thompson, G. Horsburgh, T.A. Steele, G.D. Brownlie, K.A. Prior and B.C. Cavenett 459
Quantum-confined Franz–Keldysh effect in (ZnCdSe)/(ZnSeS) quantum-well laser diodes
A.A. Toropov, T.V. Shubina, S.V. Ivanov, A.V. Lebedev, S.V. Sorokin, E.S. Oh, H.S. Park and P.S. Kop'ev 463
Interband transition and electronic subband studies in CdTe/ZnTe strained single and double quantum wells grown by double-well temperature-gradient vapor deposition
T.W. Kim and H.L. Park 467
Energy level position of Ni and band offsets in $Zn_{1-x}Cd_xSe$:Ni and ZnS_xSe_{1-x}:Ni
T.P. Surkova, W. Giriat, M. Godlewski, P. Kaczor, S.A. Permogorov and L.N. Tenishev 471
Excitons in $ZnSe_{1-x}S_x/ZnSe_{1-y}S_y$ superlattices grown by photomodulated MOCVD
S.A. Permogorov, L.N. Tenishev, A.N. Reznitsky, P.I. Kuznetsov, A.P. Chernushich, L.Yu. Zakharov and G.G. Yakushcheva 475
Composition dependent determination of band offsets in ZnCdSe/ZnSe and ZnSe/ZnSSe SQW by optical means
S. Lankes, T. Reisinger, B. Hahn, C. Meier, M. Meier and W. Gebhardt 480
Effective elastic constants in $ZnSe–ZnSe_{1-x}S_x$ strained-layer superlattices
Z.P. Guan, X.W. Fan, H. Xia, S.S. Jiang and X.K. Zhang 485
Emission mechanism of blue and green bands in ultrathin ZnSe–ZnTe superlattices
N. Takojima, Y. Ishizuka, I. Tsubono, N. Kimura, K. Suzuki, T. Sawada and K. Imai 489
Optical and electrical properties of new carrier barrier layer structure of II–VI compounds
N. Teraguchi, H. Mouri, Y. Tomomura, A. Suzuki, J. Rorison and G. Duggan 493
Band-offset determination in $Zn_{1-x}Cd_xSe$/ZnSe multiple quantum wells
V. Pellegrini, A. Tredicucci, F. Beltram, L. Vanzetti, M. Lazzarino and A. Franciosi 498
Model calculations for n-CdZnS light emitter grown on p-GaN hole injector
J.O. McCaldin, M.W. Wang and T.C. McGill 502
Optical characterization of MOVPE-grown ZnS–ZnSe short period superlattices
T. Cloitre, P. Bigenwald, B. Gil, O. Briot, N. Briot and R.L. Aulombard 506
Growth, structural and optical characterization of MBE ZnCdSe/ZnSe quantum wells
T. Reisinger, S. Lankes, M.J. Kastner, A. Rosenauer, F. Franzen, M. Meier and W. Gebhardt 510
Diffusion induced disordering (DID) in ZnSSe/ZnSe superlattices
M. Kuttler, M. Grundmann, R. Heitz, U.W. Pohl, D. Bimberg, H. Stanzel, B. Hahn and W. Gebhardt 514
Photo- and cathodoluminescence of ZnSSe quantum well heterostructures grown by MOVPE
A.L. Gurskii, E.V. Lutsenko, G.P. Yablonskii, V.I. Kozlovsky, A.B. Krysa, J. Söllner, M. Scholl, H. Hamadeh and M. Heuken 518
Optics and magneto-optics of ZnSe heteroepitaxial layers
G.N. Aliev, R.M. Datsiev, S.V. Ivanov, P.S. Kop'ev, R.P. Seisyan and S.V. Sorokin 523
Photomodulated reflectivity of $Zn_{1-x}Mn_xTe$/ZnTe multiple quantum wells
P.J. Klar, D. Wolverson, D.E. Ashenford and B. Lunn 528
Interplay between localized and free exciton recombination in CdZnSe/ZnSe multi quantum well structures
M. Godlewski, J.P. Bergman, B. Monemar, E. Kurtz and D. Hommel 533
Anisotropic center-of-mass quantization of excitons in CdTe/CdZnTe quantum wells
C. Gourgon, L.S. Dang and H. Mariette 537
Band structure and band offsets in $Zn_{1-x}Cd_xSe$/ZnSe quantum wells
M. Livingstone and I. Galbraith 542
Spectroscopy of biexcitons in $Zn_{1-x}Cd_xSe$/ZnSe strained-layer quantum wells
C. Morhain, E. Tournié, G. Neu, C. Ongaretto and J.P. Faurie 546

CdS–CdSe and CdS–ZnSe intrinsic Stark superlattices
I.V. Bradley, J.P. Creasey, K.P. O'Donnell, P.J. Wright and B. Cockayne 551

SECTION V. LASER DIODES AND LEDS

V.1. Devices and fabrication

II–VI blue-green light emitters *
A. Ishibashi 555
On the growth and doping of blue–green emitting ZnSe laser diodes *
D. Hommel, T. Behr, E. Kurtz, B. Jobst, K. Schüll, A. Jakobs, J. Nürnberger, S. Einfeldt, M. Behringer and G. Landwehr 566
Characterization of low defect density blue–green lasers *
J. Petruzello, K.W. Haberern, S.P. Herko, T. Marshall, J.M. Gaines, S. Guha, G.D. U'Ren and G.M. Haugen 573
Lateral waveguiding in blue-green II–VI semiconductor lasers
M. Buijs, R. Tijburg, K. Haberern and J. Gaines 582
Effect of ZnSe/ZnSSe superlattice buffer on improved emission efficiency of ZnCdSe/MgZnSSe quantum wells for MgZnSSe-based blue/green lasers
Y. Ichimura, K. Kishino, M. Haraguchi and A. Yoshida 586
Gain-coupled distributed feedback lasers in the blue-green spectral range by focused ion beam implantation
D. Eisert, G. Bacher, N. Mais, J.P. Reithmaier, A. Forchel, B. Jobst, D. Hommel and G. Landwehr 591
Design and fabrication of ZnSe-based blue/green surface emitting lasers
T. Honda, T. Sakaguchi, F. Koyama, K. Iga, K. Inoue, H. Munekata and H. Kukimoto 595
Degradation of microgun-pumped blue lasers
D. Hervé, J.M. Bonard, L. Vanzetti, J.J. Paggel, L. Sorba, J.D. Ganière, E. Molva and A. Franciosi 600
Magnetic tuning of resonance in semimagnetic semiconductor microcavities
H. Ulmer-Tuffigo, F. Kany, G. Feuillet, R. Langer, J. Bleuse and J.L. Pautrat 605
Electron-beam pumped laser structures based on MBE grown ZnCdSe/ZnSe superlattices
V.I. Kozlovsky, E.A. Shcherbakov, E.M. Dianov, A.B. Krysa, A.S. Nasibov and P.A. Trubenko 609
Emission wavelength and cavity design dependence of laser behaviour in HgCdTe heterostructures
J. Bonnet-Gamard, J. Bleuse, N. Magnea and J.L. Pautrat 613
Electron beam pumping of CdZnSe quantum well laser structures using a variableenergy electron beam
C. Trager-Cowan, D.M. Bagnall, F. McGow, W. McCallum, K.P. O'Donnell, P.C. Smith, P.J. Wright, B. Cockayne, K.A. Prior, J.T. Mullins, G. Horsburgh and B.C. Cavenett 618
Optimization of the waveguide properties for ZnSe laser diodes
A. Jakobs, D. Hommel and G. Landwehr 623
Growth of II–VI Bragg mirrors by molecular beam epitaxy
K. Rakennus, P. Uusimaa, J. Näppi, A. Salokatve, M. Pessa, T. Aherne, J.P. Doran, J. O'Gorman and J. Hegarty 628
Compound source molecular beam epitaxy for II–VI laser structures
K. Ohkawa, A. Tsujimura, T. Nishikawa, S. Yoshii, T. Yokogawa, M. Kubo and Y. Sasai 632
Optical properties of a ZnSSe microcavity fabricated by epitaxial lift-off
T. Aherne, A.L. Bradley, J.P. Doran, J. O'Gorman, J.F. Heffernan, J. Hegarty, H. De Neve, C. Brys, G. Geens, P. Van Daele, R. Baets, P. Demeester, K. Rakennus, A. Salokatve, P. Uusimaa and M. Pessa 636
Room temperature blue electroluminescence from the ZnMgCdSe quaternary system
S.O. Ferreira, H. Sitter, R. Krump, W. Faschinger and G. Brunthaler 640

V.2. Recombination process and gain

II–VI lasers – new directions *
A.V. Nurmikko, H. Jeon, R.L. Gunshor and J. Han 644
A study of internal losses in CdZnSe/ZnSe multiple quantum well materials
J.F. Donegan, C. Jordan, P. Rees, F. Logue, J.F. Heffernan and J. Hegarty 653
Time-resolved study of stimulated emission in ZnSe/Zn(S,Se) superlattices
M. Dabbicco, C.J. Stevens, R.A. Adams, R.A. Taylor, J.F. Ryan, R. Cingolani and I. Suemune 657
Bleaching of excitonic absorption in II–VI laser diodes under lasing conditions
A. Diessel, W. Ebeling, J. Gutowski, B. Jobst, K. Schüll, D. Hommel, M.F. Pereira, Jr., H. Güldner and K. Henneberger 661
A comparison of lasing mechanisms in ZnSe and GaAs
I. Galbraith and S.W. Koch 667

Room temperature excitonic lasing in CdTe/CdMnTe multi-quantum-well heterostructures
P. Alleysson, J. Cibert, G. Feuillet and L.S. Dang 672
Effect of external uniaxial stress on the green-blue emission of a CdZnSe strained quantum well under high excitation
T. Miyake, C. Onodera, Y. Yamada and T. Taguchi 676
Laser emission in CdZnTe/CdMnTe double quantum well heterostructures
L. Kowalczyk, G. Karczewski, T. Wojtowicz and J. Kossut 680
Overexcited CdSe quantum well lasers
D.M. Bagnall, P.G. Middleton, F. Torabi-Goudarzi, K.P. O'Donnell, P.J. Wright and B. Cockayne 684
Stimulated and spontaneous emission studies in $ZnS_{1-x}Te_x$/ZnSe strain layer superlattices
K.S. Wong, H. Wang, I.K. Sou, G.K.L. Wong and D.J. Mowbray 689

SECTION VI. CONTACTS AND SURFACES

Reconstruction and stoichiometry of CdTe(001) surfaces: a grazing incidence X-ray diffraction and reflection high energy electron diffraction study *
M.B. Veron, V.H. Etgens, M. Sauvage-Simkin, S. Tatarenko, B. Daudin and D. Brun-Le Cunff 694
Structural properties of ZnSe/GaAs(100) heterostructures with engineered band offsets
G. Bratina, L. Vanzetti, A. Bonanni, L. Sorba, J.J. Paggel, A. Franciosi, T. Peluso and L. Tapfer 703
Cd-based Ohmic contact materials to p-ZnSe
Y. Koide, K. Hashimoto, H. Ishikawa, K. Tsukui, T. Oku, M. Murakami, N. Teraguchi, Y. Tomomura and A. Suzuki 709
Effect of N-doped ZnTe layers on ZnSe/ZnTe graded superlattices
A. Taike, M. Momose, M. Kawata, J. Gotoh and K. Mochizuki 714
Improved contact resistance to n-type wide gap II–VI semiconductors
M. Lazzarino, T. Ozzello, G. Bratina, L. Vanzetti, J.J. Paggel, L. Sorba and A. Franciosi 718
Electrical contacts to p-ZnTe
J.T. Trexler, J.J. Fijol, L.C. Calhoun, R.M. Park and P.H. Holloway 723
Discrete Schottky barriers observed for the metal/n-ZnSe(100) system
C.J. Blomfield, I.M. Dharmadasa, K.A. Prior and B.C. Cavenett 727
The preparation of Sb contacts to molecular beam epitaxial ZnSe on GaAs(100) monitored by Raman spectroscopy
A. Schneider, D. Drews, D.R.T. Zahn, D. Wolfframm and D.A. Evans 732
Ultraviolet photoemission experiments on HgTe (110) cleaved surfaces
M. Banouni, M. Nasser and G. Leveque 736
Optical anisotropy of the ZnSe/GaAs interface
Z. Yang, I.K. Sou, Y.H. Yeung and G.K.L. Wong 741
AES analysis of plasma-etched ZnSe
E. Wirthl, H. Straub, M. Schmid, H. Sitter, P. Bauer and G. Brunthaler 746
Reduction of p-ZnTe/p-ZnSe valence band discontinuity by a Ga_2Se_3 interfacial layer
T. Yoshida, T. Nagatake, M. Kobayashi and A. Yoshikawa 750
Chemical preparation of ordered CdTe(110) and (100) surfaces using atomic hydrogen
D.A. Slater, Y. Luo and R.M. Osgood, Jr. 754
The growth start on the heterovalent GaAs–ZnSe interface under Te, Se and Zn termination
W. Spahn, H.R. Ress, K. Schüll, M. Ehinger, D. Hommel and G. Landwehr 761

SECTION VII. OPTICS

VII.1. General

The nonlinear behaviour of II–VI materials *
B.S. Wherrett 766
$\chi^{(3)}$ Nonlinear susceptibility in II–VI compounds and applications for squeezed light generation in semiconductors *
A.M. Fox, M. Dabbicco, J.J. Baumberg, B. Huttner and J.F. Ryan 771
Acceptor bound biexcitons in ZnSe and CdS
V. Kutzer, B. Lummer, R. Heitz, A. Hoffmann, I. Broser, E. Kurtz and D. Hommel 776
Coherent exciton–exciton interaction in wide-gap II–VI quantum wells. The role of alloy disorder
H. Nickolaus, F. Henneberger and A. Schülzgen 780
Bound- and bi-excitons in ZnCdSe/ZnSe multiple quantum wells
J. Puls, V.V. Rossin, F. Kreller, H.-J. Wünsche, St. Renisch, N. Hoffmann, M. Rabe and F. Henneberger 784

Dynamics of band filling and of stimulated emission in $CdS_{1-x}Se_x$ and $Zn_{1-y}Cd_yS$ alloys
T. Breitkopf, A. Reznitsky, H. Kalt and C. Klingshirn 788
Excitonic nonlinearities in wide gap II–VI multiple quantum wells
L. Calcagnile, G. Coñ, M. De Vittorio, R. Rinaldi, P.V. Giugno, R. Cingolani, L. Vanzetti, L. Sorba and A. Franciosi 793
Propagation of exciton polaritons in $ZnSe/ZnS_xSe_{1-x}$
K. Wundke, U. Neukirch, F. Kubacki, J. Gutowski and D. Hommel 800
Picosecond optical bistability in ZnSe–CdZnSe multiple quantum wells with a Fabry–Pérot cavity
D.Z. Shen, J.Y. Zhang, S.M. Wang, B.J. Yang and X.M. Fan 805
Continuous wave half-gap second-harmonic generation in ZnCdSe/ZnSe asymmetric coupled quantum wells
V. Pellegrini, A. Parlangeli, M. Börger, F. Beltram, L. Vanzetti and A. Franciosi 809
Dynamics of dense excitonic systems in ZnSe-based single quantum wells
Y. Yamada, T. Mishina, Y. Masumoto, Y. Kawakami, J. Suda, Sz. Fujita, Sg. Fujita and T. Taguchi 814
Electron tunnelling in CdTe/CdMnTe double barrier structures
N. Cain, M. O'Neill, J.E. Nicholls, T. Piorek, W.E. Hagston, P. Chen, S. Chalk, D.E. Ashenford, A.J. Langley and P.F. Taday 818
Exciton recombination dynamics in ZnCdSe/ZnSe quantum wells
R.A. Taylor, R.A. Adams, J.F. Ryan and R.M. Park 822
Optical studies in ZnSe/GaAs epilayers: Fabry–Perot modes in the upper branch of the polariton
C. Boemare, B. Gil, M. Assunçao and M.H. Nazare 826
Effects of high excitation on localized excitons in cubic ZnCdS lattice matched to GaAs
Y. Kawakami, M. Funato, Sz. Fujita, Sg. Fujita, Y. Yamada, T. Mishina and Y. Masumoto 830
Ultrafast electric field induced nonlinear response in ZnSe/ZnSeS superlattices
C.J. Stevens, M. Dabbicco, R.A. Taylor and J.F. Ryan 835
Picosecond photoluminescence properties of CdTe–ZnTe superlattices prepared by hot-wall epitaxy
H. Kuwabara, H. Asai, H. Tatsuoka, T. Nakamura, Y. Nakanishi and H. Fujiyasu 839
Effects of spatial dispersion in the temperature dependence of the optical absorption in ZnSe heteroepitaxial layers and CdTe and ZnTe crystals
G.N. Aliev, R.P. Seisyan and O. Coschug-Toates 843
Phonon sidebands in luminescence spectra of alloy-trapped excitons in disordered solid solutions
A.A. Klochikhin, S.A. Permogorov and A.N. Reznitsky 848

VII.2. Nanocrystals

Optical properties of Mn-doped CdS nanocrystals
M.A. Chamarro, V. Voliotis, R. Grousson, P. Lavallard, T. Gacoin, G. Counio, J.P. Boilot and R. Cases 853
Optical properties of ordered three-dimensional arrays of structurally confined semiconductors
S.G. Romanov, A.V. Fokin, V.V. Tretijakov, V.Y. Butko, V.I. Alperovich, N.P. Johnson and C.M. Sotomayor Torres 857
Influence of growth conditions on the structural properties of CdS_xSe_{1-x} ($x = 0.4$ and $x = 1$) nanocrystals
C. Ricolleau, L. Audinet, M. Gandais, T. Gacoin, J.-P. Boilot and M. Chamarro 861
Gain processes in CdSe quantum dots
O. Wind, F. Gindele, U. Woggon and C. Klingshirn 867
Giant electric field in photo-darkened CdS_xSe_{1-x} semiconductor doped glasses
A. Vanhaudenarde-Péoc'h, C. Moussu and R. Frey 871

SECTION VIII. DEFECTS

Optical and magnetic properties of Fe^{2+} and Cr^{2+} in II–VI semiconductors: the Jahn–Teller effect
D. Colignon, E. Kartheuser, S. Rodriguez and M. Villeret 875
Photoluminescence of p-CdTe: characterization of impurity centers by phonon sidebands
M. Certier, M. Soltani, R. Evrard and E. Kartheuser 879
Dislocation-related absorption and photoluminescence in deformed n-ZnSe crystals
Y.G. Shreter, Y.T. Rebane, O.V. Klyavin, P.S. Aplin, C.J. Axon, W.T. Young and J.W. Steeds 883
Local vibrational modes of the CuO_4-cluster in ZnO
I. Broser, G. Kaczmarczyk, P. Thurian, R. Heitz and A. Hoffmann 889

SECTION IX. OTHER DEVICES

Modulator and saturable absorber for integration with CdZnSe/ZnSe/ZnMgSSe QW-laser diodes
W. Ebeling, B.S. Ryvkin, J. Gutowski, K. Schüll, B. Jobst and D. Hommel 893

Electro-optical modulation in the blue–green spectral range using ZnSe-based waveguides
H. Babucke, P. Thiele, T. Prasse, V. Egorov, M. Rabe and F. Henneberger 898
ZnSe/ZnCdSe quantum confined Stark effect waveguide modulator
P.J. Thompson, S.Y. Wang, G. Horsburgh, T.A. Steele, K.A. Prior and B.C. Cavenett 902
Performance of MBE grown CdTe photoconductor arrays for hard X-ray detection
S.S. Yoo, B. Rodricks, J.P. Faurie, S. Sivananthan and P.A. Montano 906
Dependence of CdS/CdTe thin film solar cell characteristics on the processing conditions
H.M. Al-Allak, A.W. Brinkman, H. Richter and D. Bonnet 910
Characterisation of in-situ thermally evaporated CdS/CdTe thin film solar cells with Ni–P back contacts
S. Duke, R.W. Miles, P.C. Pande, S. Spoor, B. Ghosh, P.K. Datta, M.J. Carter and R. Hill 916
Investigation of p–i–n solar cell efficiency enhancement by use of MQW structures in the i-region
D.E. Ashenford, A.W. Dweydari, D. Sands, C.G. Scott, M. Yousaf, E. Aperathitis, Z. Hatzopoulos and P. Panayotatos 920
A study of CdS/CdTe thin film solar cells using beam injection techniques
S.A. Galloway, A.J. Holland and K. Durose 925
Recrystallisation of electrophoretically deposited CdTe films
P.C. Pande, S. Bocking, S. Duke, R.W. Miles, M.J. Carter, I.D. Latimer and R. Hill 930
Investigations of the influence of halides on the properties of CeX_3-doped (X = Cl, F) strontium sulphide thin film electroluminescence devices
T.A. Oberacker and H.W. Schock 935
Enhancement of fluorescence and related spectra in $Ca_{1-x}Sr_xS$ with cadmium incorporation
S. Clough, J.C. Bickerton, J.W. Brightwell, B. Ray and I.V.F. Viney 939
SrS:Ce,Mn,Cl – a novel efficient EL phosphor
B. Hüttl, K.O. Velthaus, U. Troppenz, R. Herrmann and R.H. Mauch 943

SECTION X. DILUTE MAGNETIC SEMICONDUCTORS

Spin dependent carrier localization in Fe-based semimagnetic semiconductor heterostructures *
B.T. Jonker, H. Abad, W.Y. Yu, S. Stoltz, A. Petrou, J. Warnock, C.D. Poweleit, L.M. Smith and T. Schmiedel 947
Molecular-beam epitaxy of mercury–iron selenide layers and quantum wells *
D. Schikora, Th. Widmer, K. Lischka, P. Schäfer, G. Machel, S. Luther and M. von Ortenberg 959
Magnetic-field induced type I–type II transition in $CdTe/Cd_{1-x}Mn_xTe$ multiple quantum wells
S. Kuroda, K. Kojima, K. Takita, K. Uchida and N. Miura 967
Ferromagnetism in Cr-based diluted magnetic semiconductors
J. Blinowski, P. Kacman and J.A. Majewski 972
Dynamics of exciton magnetic polarons in $Cd_{1-x}Mn_xTe/Cd_{1-x-y}Mn_xMg_yTe$ quantum wells
R. Hellmann, A. Euteneuer, E.O. Göbel, G. Mackh, D.R. Yakovlev, A. Waag and G. Landwehr 976
Manganese diffusion in MBE-grown Cd(Mn)Te structures
A. Barcz, G. Karczewski, T. Wojtowicz and J. Kossut 980
Dynamics of the magnetic polaron formation in ZnSe/ZnMnSe quantum well structures
V.V. Rossin, F. Henneberger and J. Puls 985
Exciton dynamics in MBE grown CdTe/CdMnTe multiple quantum wells
M. Godlewski, M. Surma, G. Karczewski, J. Jaroszyński, T. Wojtowicz, J. Kossut, J.P. Bergman and B. Monemar 989
The s,p–d exchange interaction in $Zn_{1-x}Cr_xTe$ diluted magnetic semiconductors
W. Mac, Nguyen The Khoi, A. Twardowski and M. Demianiuk 993
Magneto-optical study of the exchange interaction in (Cd,Mn)Te under high hydrostatic pressure
R. Meyer, M. Dahl, G. Schaack, A. Waag and R. Boehler 997
Polarization properties of multiple Mn^{2+}-spin-flip Raman scattering in semimagnetic quantum wells
J. Stühler, G. Schaack, M. Dahl, A. Waag, G. Landwehr, K.V. Kavokin and I.A. Merkulov 1001
Dimensional dependence of magneto-optical properties of ZnMnSe MBE layers
W. Heimbrodt, L. Gridneva, M. Happ, F. Neugebauer, D. Suisky, N. Hoffmann and J. Griesche 1005
Optically detected spin-glass transition in superlattices and quantum wells of diluted magnetic semiconductors
M. Dahl, A. Mergler, M. Sawicki, T. Litz, A. Waag, T. Gerhard, G. Karczewski, T. Wojtowicz and J. Kossut 1009
Exciton tunnelling and resonances in semimagnetic double-quantum-well structures
K. Hieke, W. Heimbrodt, Th. Pier, H.-E. Gumlich, W.W. Rühle, J.E. Nicholls and B. Lunn 1014
On the d–d exchange interaction in Mn-alloyed semimagnetic semiconductors
H. Bednarski and J. Cisowski 1018
Epitaxial growth and magneto-optical study of ferromagnetic-MnSb/antiferromagnetic-MnTe heterostructures
H. Akinaga, S. Miyanishi, Y. Suzuki, K. Tanaka, T. Katayama and K. Ando 1022

Anisotropic magnetic field effects in diluted magnetic semiconductor quantum wells
T. Stirner, S. Ahmed and W.E. Hagston 1027
Towards a dynamical theory of magnetic polaron formation
J. Miao, T. Stirner and W.E. Hagston 1032
Magnetic field induced transitions in diluted magnetic semiconductor quantum wells
T. Piorek, P. Harrison, T. Stirner and W.E. Hagston 1037
Carrier generation and multiplication in ZnS:Mn: investigation ofluminescence excitation by synchrotron radiation
H.-E. Gumlich, H.-Ch. Mertins and Ch. Jung 1041
Enhanced paramagnetism in ultrathin $Cd_{1-x}Mn_xTe$ layers
W. Ossau, B. Kuhn-Heinrich, A. Waag and G. Landwehr 1046
Spin dependent confinement effects in $Cd_{0.9}Mn_{0.1}Te/Cd_{0.9}Mg_{0.1}Te$ spin superlattices
W. Ossau, B. Kuhn-Heinrich, G. Mackh, A. Waag and G. Landwehr 1052
Magnetic oscillation of many-body effects in CdTe based modulation doped quantum wells
J.X. Shen, W. Ossau, F. Fischer, A. Waag and G. Landwehr 1057
Spin-flip Raman scattering studies of $ZnSe/Zn_{1-x}Mn_xSe$ multiple quantum well structures
P.J. Klar, P.J. Boyce, D. Wolverson, J.J. Davies, W. Heimbrodt, N. Hoffmann and J. Griesche 1061
Influence of the barrier heights on vertical transport in CdTe/CdMnTe superlattices
P. Chen, J.E. Nicholls, M. O'Neill, J.H.C. Hogg, W.E. Hagston, B. Lunn and D.E. Ashenford 1066
Low temperature magnetoresistance of the persistent photoconductor $Cd_{0.9}Mn_{0.1}Te$:In
I. Terry, T. Penney, S. von Molnár and P. Becla 1070
Properties of MBE grown CdYbTe and ZnYbTe on GaAs(100) substrates
J. Sadowski, E. Dynowska, K. Szamota-Sadowska, W. Przedpełski, P. Sitarek, P. Sitarek and K. Świątek 1075

SECTION XI. NARROW GAP SEMICONDUCTORS

Properties of $Hg_{0.7}Cd_{0.3}Te/CdTe$ superlattices with semiconducting wells
T.K. Tran, A. Parikh, T. Kelz, J.W. Tomm, W. Hoerstel, P. Schäfer, B.K. Wagner, S.D. Pearson, R. Bicknell-Tassius and C.J. Summers 1080
Electrical measurements of $Hg_{1-x}Mn_xTe$ films grown by metalorganic vapour phase epitaxy
A.B. Horsfall, S. Oktik, I. Terry and A.W. Brinkman 1085
Extended defects in epitaxial cadmium mercury telluride
A. Wasenczuk, A.F.W. Willoughby, P. Mackett, E. O'Keefe, P. Capper and C.D. Maxey 1090
Precipitation and migration of point defects in MOCVD $Cd_xHg_{1-x}Te$
I.P. Jones, T.T. Cheng, M. Aindow, J. Gough, A. Graham and J. Giess 1096
Room temperature narrow gap semiconductor diodes as sources and detectors in the 5–10 μm wavelength region
T. Ashley, C.T. Elliott, N.T. Gordon, R.S. Hall, A.D. Johnson and G.J. Pryce 1100
Landau-split and spin-split cyclotron resonance of two-dimensional electron systems in HgTe quantum wells
M. von Truchsess, V. Latussek, C.R. Becker and E. Batke 1104
Short-range order and micro-inhomogeneities in $Cd_xHg_{1-x}Te$: characterisation by means of FIR and Raman spectroscopies
M.I. Vasilevskiy, O.V. Baranova, Z.F. Krasil'nik, D.A. Rakhlin and S.V. Stroganova 1108
Critical point parameters deduced from the dielectric function in HgZnTe and CdZnTe alloys
O. Castaing, J.T. Benhlal, R. Granger and R. Triboulet 1112
Determination of the migration energy of Hg interstitials in (HgCd)Te from ion milling experiments
E. Belas, R. Grill, J. Franc, A. Toth, P. Höschl, H. Sitter and P. Moravec 1117
Correlation between crystal defects and the band gap of epitaxially grown $Hg_{1-x}Zn_xSe$ on GaAs(001)
T. Behr, S. Einfeldt, D. Hommel, C.R. Becker, G. Landswehr and H. Cerva 1123
Temperature dependent investigation of the HgTe/CdTe valence band offset
M. von Truchsess, V. Latussek, C.R. Becker and E. Batke 1128
Metalorganic vapor phase epitaxial growth of hillock free (100) HgCdTe/GaAs with good electrical properties
Sang-Hee Suh, Jong-Hyeong Song and Sun-Wook Moon 1132
Doping of (211)B mercury cadmium telluride
P.S. Wijewarnasuriya, J.P. Faurie and S. Sivananthan 1136
Arrhenius results for the diffusion of Hg into CdTe
M.U. Ahmed, E.D. Jones, J.B. Mullin and N.M. Stewart 1141
Diffusion of Ag in Cd-rich mercury, cadmium telluride $Cd_xHg_{1-x}Te$ ($x = 0.55$–0.8)
I. Lyubomirsky, V. Lyakhovitskaya, R. Triboulet and D. Cahen 1148
Growth and characterization of HgCdTe heterostructures by metalorganic molecular beam epitaxy
A. Parikh, S.D. Pearson, T.K. Tran, R.N. Bicknell, R.G. Benz, B.K. Wagner, P. Schäfer and C.J. Summers 1152

The band gap of $Hg_{1-x}Mg_xTe$ grown by molecular beam epitaxy
S. Oehling, U. Lunz, H. Heinke, G. Plahl, C.R. Becker and G. Landwehr 1157
Molecular beam epitaxy of high quality $Hg_{1-x}Cd_xTe$ films with control of the composition distribution
V.S. Varavin, S.A. Dvoretsky, V.I. Liberman, N.N. Mikhailov and Yu.G. Sidorov 1161

SECTION XII. POST-DEADLINE PAPERS

ZnCdSe–MgZnSSe laser diodes fabricated by gas-source molecular beam epitaxy
M. Imaizumi, Y. Endoh, M. Suita, K. Ohtsuka, T. Isu, H. Namizaki and M. Nunoshita 1167
Direct observation of nitrogen acceptor passivation in ZnSe by hydrogen plasma
T. Yasuda, T. Yasui, B.-P. Zhang and Y. Segawa 1168
Optical studies of ZnSe–ZnS stain layer superlattices grown on sapphire by MOVPE
Liao Qi-Wei, Fan Xi-Wu and Wang Zhang-Guo 1171
Channelled-substrate planar waveguided green laser diodes
N. Nakayama, T. Kawasumi and A. Ishibashi 1172

Author index 1173

Subject index 1193